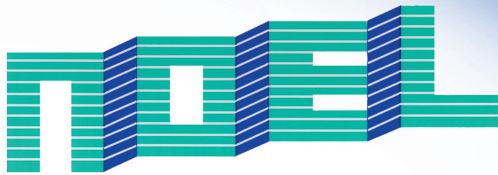

NOEL Technologies

# Plasma Etching Capabilities

- Fluorine –Based Chemistries including CF4 and SF6 with O2 and/or Argon Carrier Gas.
- Wafer sizes: 2" – 8"
- Blanket and patterned films including: PECVD Nitride, Polysilicon, a-Silicon, LPCVD Nitride, Polysilicon , a-Silicon, Thermally grown and Deposited oxides.
- Critical Dimension Features ranging from .2µm to 5mm Checkerboard patterns or Bond Pads.
- Photo resist Thickness Ranges: 6,000A – 10.0µm
- Post Etch Photo resist Removal: EKC Solvent Strip, O2 Plasma Ash or Piranha "Hot Sulfuric".
- Low Particle Post Resist Clean: SC1/SC2, Megasonic, LP Scrub
- X-Section SEMs Available upon request

Noel Technologies Inc. • 1510C Dell Ave., Campbell, CA 95008 • Tel: 408.374.9549 • Fax: 408.374.4127 • www.noeltech.com